



# PolySi passivating contact for solar cells

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## Why be interested in polySi passivating contact

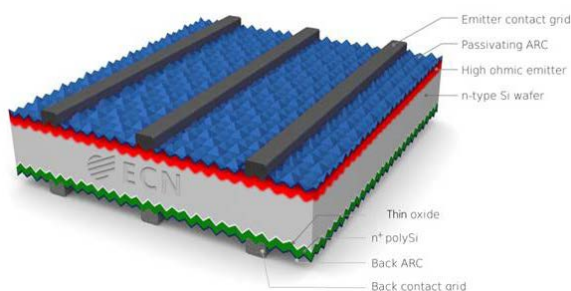
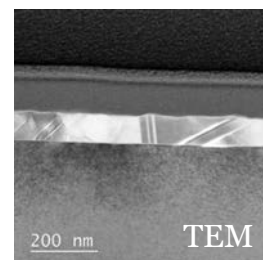
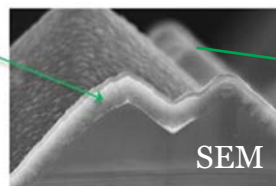
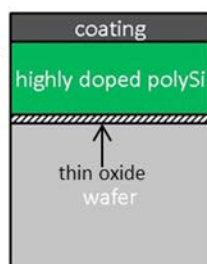
- Industrial deposition method (LPCVD)
- Excellent passivation with n-polySi
  - $iV_{oc}$  744 / 736 mV on polished/textured surface
- Very good passivation with p-polySi
  - $iV_{oc}$  727 / 701 mV on polished/textured surface
- Roadmap to > 22.5 % cell efficiency
- 6 inch cell efficiency > 21.5%, bifaciality >85%
  - with conventional emitter, and all fire-through contact

## ECN offers

- Co-development, e.g. of PERPoly cell concepts
- Technology transfer, e.g. of PERPoly process flow

## Why ECN

- The only research institute to develop a **6-inch cost effective cell process** based on **polysilicon passivating contact** and **firing through metallization**
- Many years of track record on technology transfer, with excellent results



Passivated Emitter and Rear Polysilicon solar cell

